

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74HC367AP, TC74HC367AF, TC74HC367AFN
TC74HC368AP, TC74HC368AF, TC74HC368AFN

HEX BUS BUFFER

TC74HC367AP/AF/AFN NON-INVERTED (3-STATE)
TC74HC368AP/AF/AFN INVERTED (3-STATE)

(Note) The JEDEC SOP (FN) is not available in Japan.

The TC74HC367A and TC74HC368A are high speed CMOS 3-STATE BUS BUFFERS fabricated with silicon gate C²MOS technology.

They achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

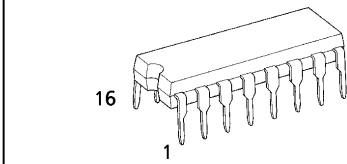
They contain six buffers; four buffers are controlled by an enable input ($\overline{G1}$), and the other two buffers are controlled by another enable input ($\overline{G2}$). The outputs of each buffer group are enabled when $\overline{G1}$ and/or $\overline{G2}$ inputs are held low; if held high, these outputs are in a high impedance state.

The TC74HC367A is a non-inverting output type, while the TC74HC368A is an inverting output type.

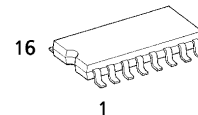
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES :

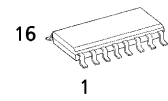
- High Speed..... $t_{pd} = 11ns(typ.)$ at $V_{CC} = 5V$
- Low Power Dissipation..... $I_{CC} = 4\mu A(Max.)$ at $T_a = 25^\circ C$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC} (Min.)$
- Output Drive Capability..... 15 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 6mA$
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range... $V_{CC} (opr.) = 2V \sim 6V$
- Pin and Function Compatible with 74LS367/368



P (DIP16-P-300-2.54A)
Weight : 1.00g (Typ.)

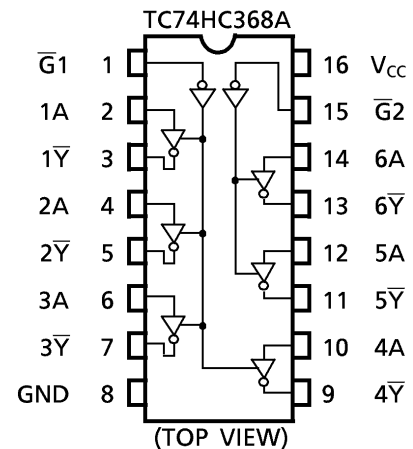
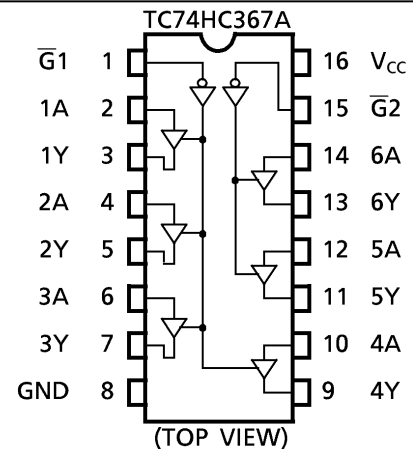


F (SOP16-P-300-1.27)
Weight : 0.18g (Typ.)



FN (SOL16-P-150-1.27)
Weight : 0.13g (Typ.)

PIN ASSIGNMENT

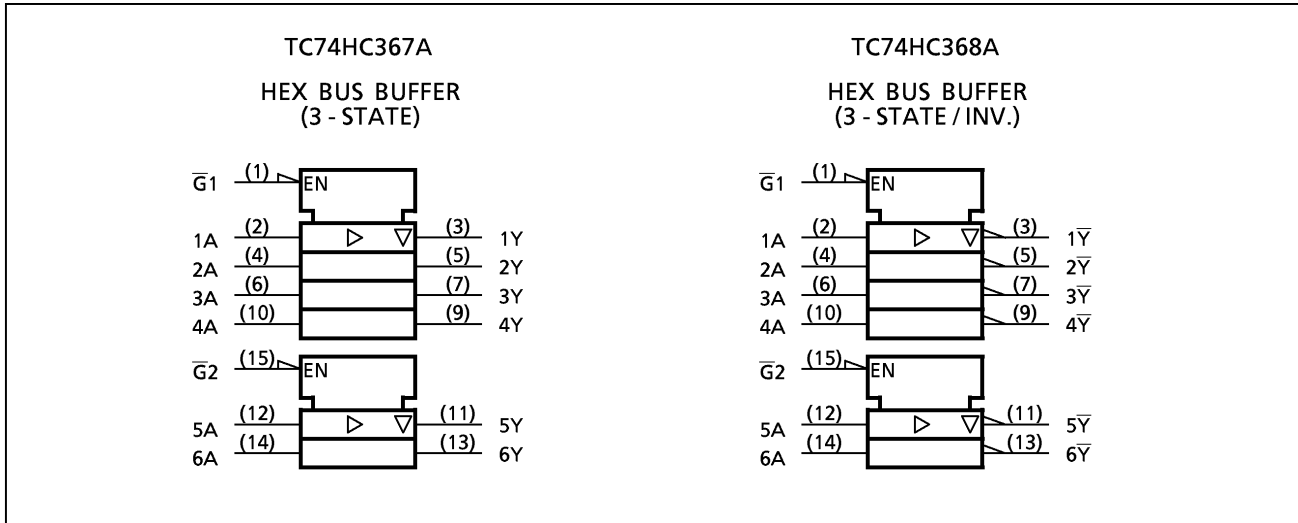


TRUTH TABLE

INPUTS		OUTPUTS	
\overline{G}	A_n	Y(367A)	\overline{Y} (368A)
L	L	L	H
L	H	H	L
H	X	Z	Z

X : Don't Care, Z : High Impedance

IEC LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC}+0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC}+0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 35	mA
DC V_{CC} /Ground Current	I_{CC}	± 75	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	-65~150	°C

*500mW in the range of $T_a = -40^\circ\text{C} \sim 65^\circ\text{C}$. From $T_a = 65^\circ\text{C}$ to 85°C a derating factor of $-10\text{mW}/^\circ\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~1000 ($V_{CC} = 2.0\text{V}$) 0~500 ($V_{CC} = 4.5\text{V}$) 0~400 ($V_{CC} = 6.0\text{V}$)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim 85^\circ\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	V_{IH}		2.0	1.50	—	—	1.50	—	V	
			4.5	3.15	—	—	3.15	—		
			6.0	4.20	—	—	4.20	—		
Low - Level Input Voltage	V_{IL}		2.0	—	—	0.50	—	0.50	V	
			4.5	—	—	1.35	—	1.35		
			6.0	—	—	1.80	—	1.80		
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -20\mu\text{A}$	2.0	1.9	2.0	—	1.9	—	V
				4.5	4.4	4.5	—	4.4	—	
			6.0	5.9	6.0	—	5.9	—		
			$I_{OH} = -6\text{ mA}$ $I_{OH} = -7.8\text{ mA}$	4.5	4.18	4.31	—	4.13	—	
6.0	5.68	5.80		—	5.63	—				
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 20\mu\text{A}$	2.0	—	0.0	0.1	—	0.1	V
				4.5	—	0.0	0.1	—	0.1	
			6.0	—	0.0	0.1	—	0.1		
			$I_{OL} = 6\text{ mA}$ $I_{OL} = 7.8\text{ mA}$	4.5	—	0.17	0.26	—	0.33	
6.0	—	0.18		0.26	—	0.33				
3 - State Output Off - State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND	6.0	—	—	± 0.5	—	± 5.0	μA	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	± 0.1	—	± 1.0		
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	4.0	—	40.0		

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT		
			CL	V _{CC} (V)	MIN.	TYP.	MAX.		MIN.	MAX.
Output Transition Time	t_{TLH} t_{THL}		50	2.0	—	25	60	—	75	ns
				4.5	—	7	12	—	15	
				6.0	—	6	10	—	13	
Propagation Delay Time	t_{pLH} t_{pHL}		50	2.0	—	36	95	—	120	
				4.5	—	12	19	—	24	
				6.0	—	10	16	—	20	
			150	2.0	—	40	130	—	165	
				4.5	—	16	26	—	33	
				6.0	—	14	22	—	28	
Output Enable Time	t_{pZL} t_{pZH}	$R_L = 1\text{k}\Omega$	50	2.0	—	36	120	—	150	
				4.5	—	12	24	—	30	
				6.0	—	10	20	—	26	
			150	2.0	—	40	160	—	200	
				4.5	—	16	32	—	40	
				6.0	—	14	27	—	34	
Output Disable Time	t_{pLZ} t_{pHZ}	$R_L = 1\text{k}\Omega$	50	2.0	—	35	120	—	150	
				4.5	—	15	24	—	30	
				6.0	—	13	20	—	26	
Input Capacitance	C_{IN}				—	5	10	—	pF	
Output Capacitance	C_{OUT}				—	10	—	—		
Power Dissipation Capacitance	C_{PD} (1)	TC74HC367A			—	36	—	—		—
		TC74HC368A			—	30	—	—	—	

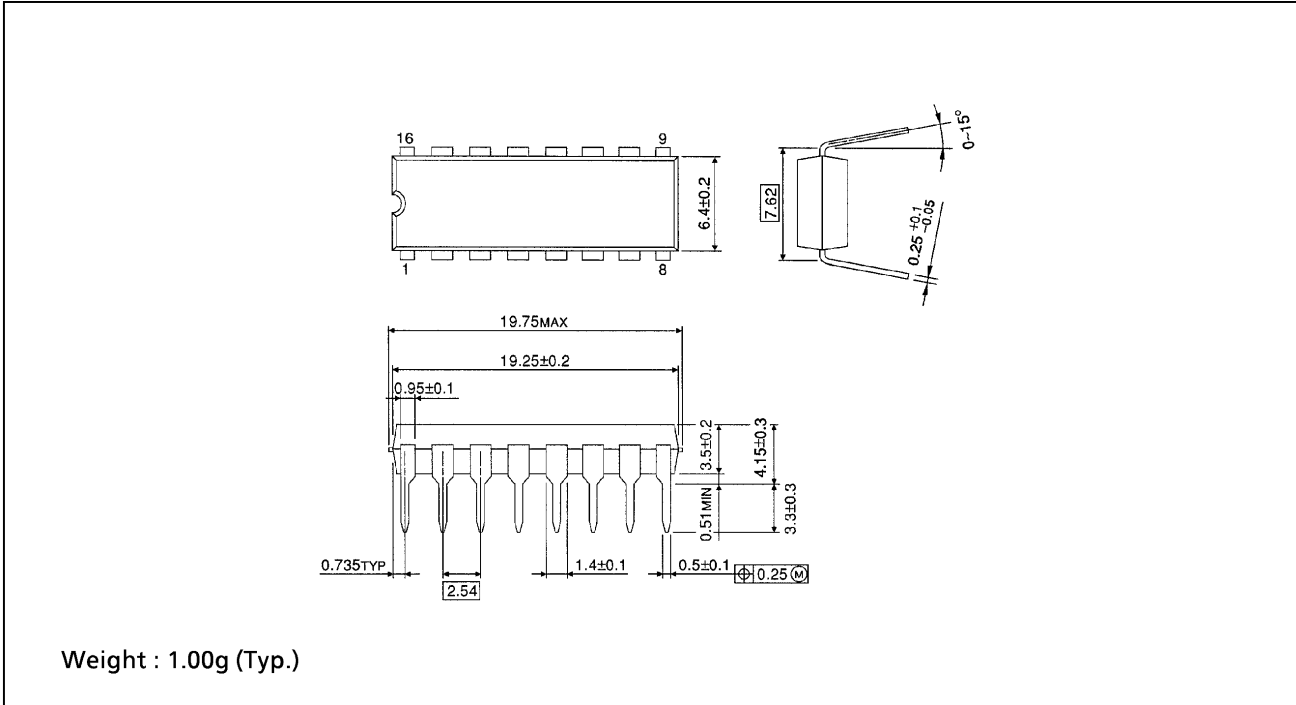
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 \text{ (per bit)}$$

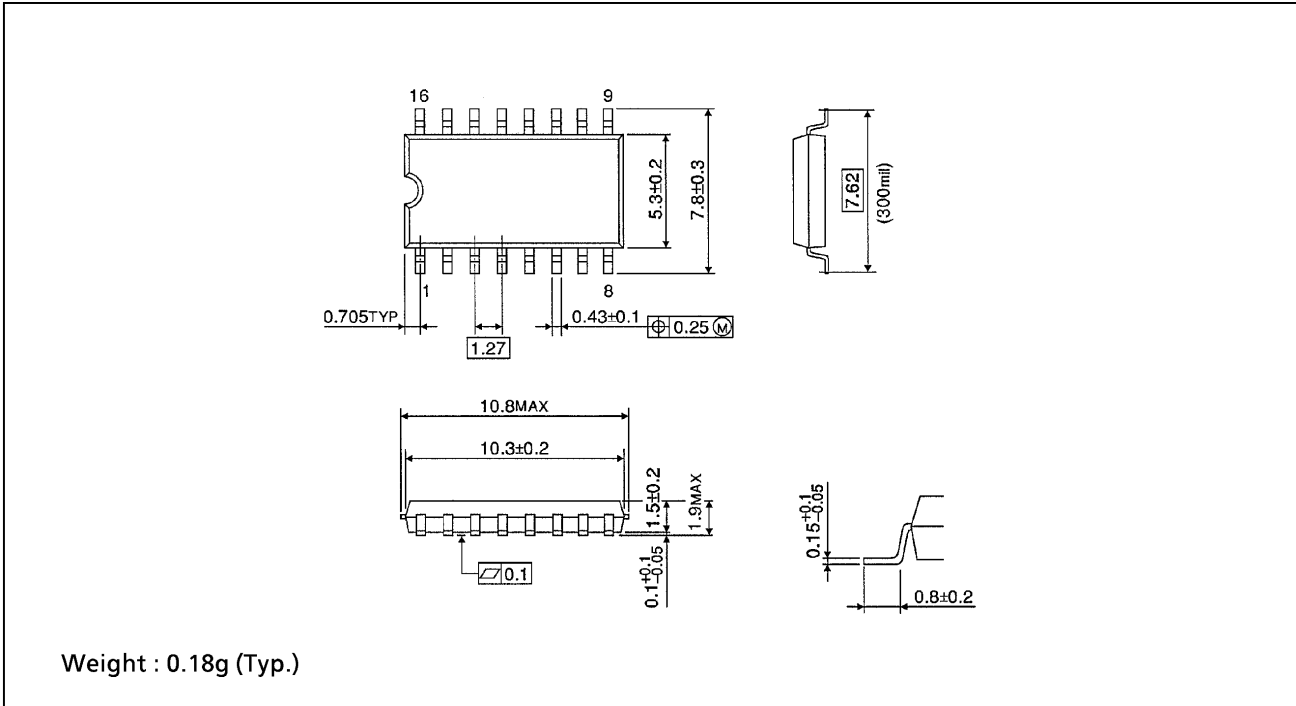
DIP 16PIN PACKAGE DIMENSIONS (DIP16-P-300-2.54A)

Unit in mm



SOP 16PIN (200mil BODY) PACKAGE DIMENSIONS (SOP16-P-300-1.27)

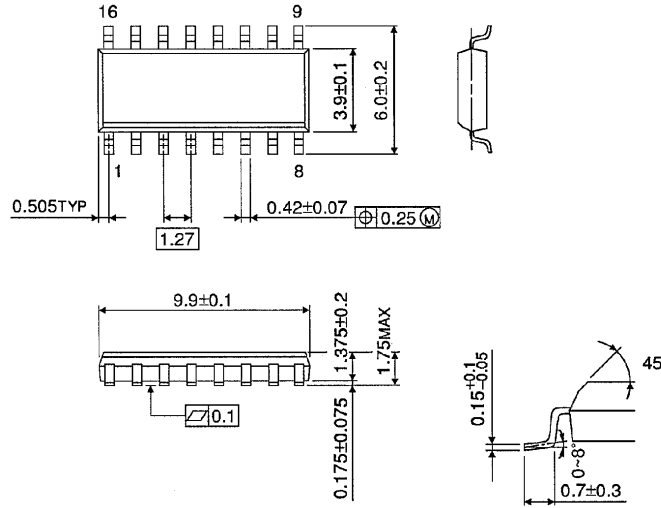
Unit in mm



SOP 16PIN (150mil BODY) PACKAGE DIMENSIONS (SOL16-P-150-1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.13g (Typ.)

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000707EBA

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